

SOJ, TSOP, FP-BGA
Commercial Temp
Industrial Temp
64K x 16
1Mb Asynchronous SRAM
6, 8, 10, 12 ns
3.3 V V_{DD}
Center V_{DD} and V_{SS}

Features

- Fast access time: 6, 8, 10, 12 ns
- CMOS low power operation: 165/125/100/85 mA at minimum cycle time
- Single 3.3 V power supply
- All inputs and outputs are TTL-compatible
- Byte control
- Fully static operation
- Industrial Temperature Option: -40° to 85°C
- Package line up
 - J: 400 mil, 44-pin SOJ package
 - TP: 400 mil, 44-pin TSOP Type II package
 - U: 6 mm x 8 mm Fine Pitch Ball Grid Array package

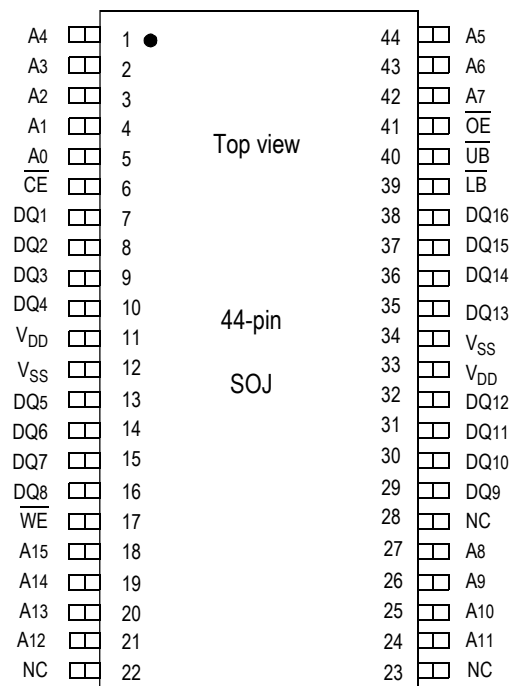
Description

The GS71116A is a high speed CMOS static RAM organized as 65,536-words by 16-bits. Static design eliminates the need for external clocks or timing strobes. Operating on a single 3.3 V power supply and all inputs and outputs are TTL-compatible. The GS71116A is available in a 6 mm x 8 mm Fine Pitch BGA package, as well as in 400 mil SOJ and 400 mil TSOP Type-II packages.

Pin Descriptions

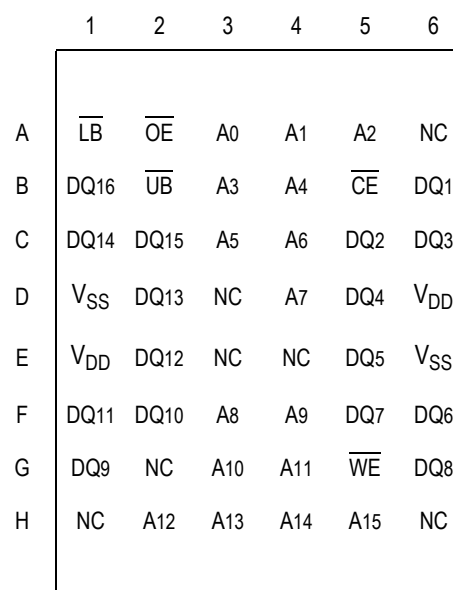
Symbol	Description
A0–A15	Address input
DQ1–DQ16	Data input/output
CE	Chip enable input
$\overline{\text{LB}}$	Lower byte enable input (DQ1 to DQ8)
$\overline{\text{UB}}$	Upper byte enable input (DQ9 to DQ16)
WE	Write enable input
OE	Output enable input
V_{DD}	+3.3 V power supply
V_{SS}	Ground
NC	No connect

SOJ 64K x 16-Pin Configuration



Package J

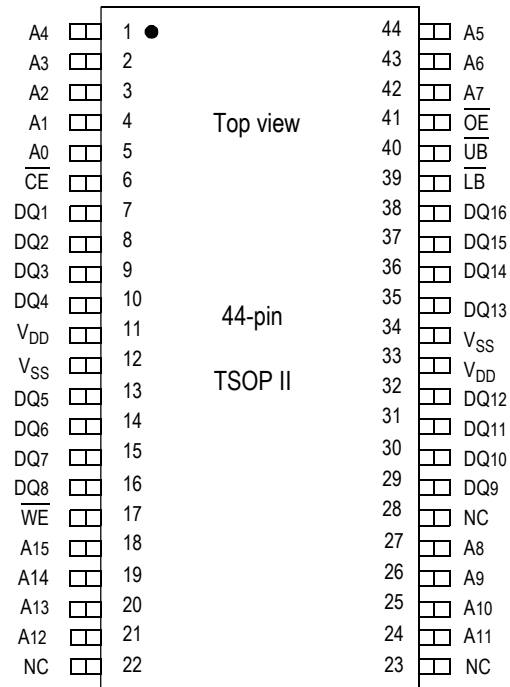
Fine Pitch BGA 64K x 16-Bump Configuration



6 mm x 8 mm, 0.75 mm Bump Pitch (Package U)

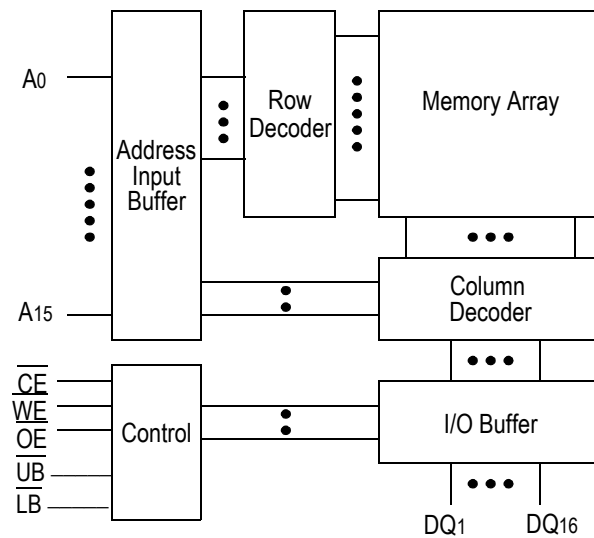
Top View

TSOP-II 64K x 16-Pin Configuration



Package TP

Block Diagram



Truth Table

$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	$\overline{\text{LB}}$	$\overline{\text{UB}}$	DQ1 to DQ8	DQ9 to DQ16	V_{DD} Current
H	X	X	X	X	Not Selected	Not Selected	ISB1, ISB2
L	L	H	L	L	Read	Read	I_{DD}
			L	H	Read	High Z	
			H	L	High Z	Read	
L	X	L	L	L	Write	Write	
			L	H	Write	Not Write, High Z	
			H	L	Not Write, High Z	Write	
L	H	H	X	X	High Z	High Z	
L	X	X	H	H	High Z	High Z	

Note: X: "H" or "L"

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply Voltage	V_{DD}	−0.5 to +4.6	V
Input Voltage	V_{IN}	−0.5 to V_{DD} +0.5 (≤ 4.6 V max.)	V
Output Voltage	V_{OUT}	−0.5 to V_{DD} +0.5 (≤ 4.6 V max.)	V
Allowable power dissipation	PD	0.7	W
Storage temperature	T_{STG}	−55 to 150	°C

Note:

Permanent device damage may occur if Absolute Maximum Ratings are exceeded. Functional operation shall be restricted to Recommended Operating Conditions. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage for -8/-10/-12	V_{DD}	3.0	3.3	3.6	V
Supply Voltage for -6	V_{DD}	3.135	3.3	3.6	V
Input High Voltage	V_{IH}	2.0	—	$V_{DD} + 0.3$	V
Input Low Voltage	V_{IL}	-0.3	—	0.8	V
Ambient Temperature, Commercial Range	T_{Ac}	0	—	70	°C
Ambient Temperature, Industrial Range	T_{AI}	-40	—	85	°C

Notes:

1. Input overshoot voltage should be less than $V_{DD} + 2$ V and not exceed 20 ns.
2. Input undershoot voltage should be greater than -2 V and not exceed 20 ns.

Capacitance

Parameter	Symbol	Test Condition	Max	Unit
Input Capacitance	C_{IN}	$V_{IN} = 0$ V	5	pF
Output Capacitance	C_{OUT}	$V_{OUT} = 0$ V	7	pF

Notes:

1. Tested at $T_A = 25^\circ\text{C}$, $f = 1$ MHz
2. These parameters are sampled and are not 100% tested.

DC I/O Pin Characteristics

Parameter	Symbol	Test Conditions	Min	Max
Input Leakage Current	I_{IL}	$V_{IN} = 0$ to V_{DD}	-1 μA	1 μA
Output Leakage Current	I_{LO}	Output High Z $V_{OUT} = 0$ to V_{DD}	-1 μA	1 μA
Output High Voltage	V_{OH}	$I_{OH} = -4$ mA	2.4	
Output Low Voltage	V_{OL}	$I_{LO} = +4$ mA		0.4V

Power Supply Currents

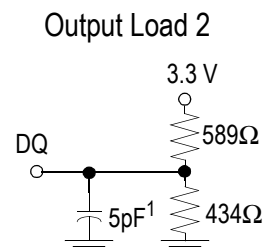
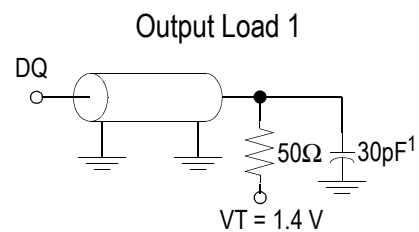
Parameter	Symbol	Test Conditions	0 to 70°C				-40 to 85°C			
			6 ns	8 ns	10 ns	12 ns	6 ns	8 ns	10 ns	12 ns
Operating Supply Current	I _{DD}	$\overline{CE} \leq V_{IL}$ All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ Min. cycle time I _{OUT} = 0 mA	165 mA	125 mA	100 mA	85 mA	170 mA	130 mA	105 mA	90 mA
Standby Current	I _{SB1}	$\overline{CE} \geq V_{IH}$ All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ Min. cycle time	25 mA	20 mA	20 mA	15 mA	30 mA	25 mA	25 mA	20 mA
Standby Current	I _{SB2}	$\overline{CE} \geq V_{DD} - 0.2 V$ All other inputs $\geq V_{DD} - 0.2 V$ or $\leq 0.2 V$	2 mA				5 mA			

AC Test Conditions

Parameter	Conditions
Input high level	$V_{IH} = 2.4 \text{ V}$
Input low level	$V_{IL} = 0.4 \text{ V}$
Input rise time	$t_r = 1 \text{ V/ns}$
Input fall time	$t_f = 1 \text{ V/ns}$
Input reference level	1.4 V
Output reference level	1.4 V
Output load	Fig. 1 & 2

Notes:

1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown in **Fig. 1** unless otherwise noted.
3. Output load 2 for t_{LZ} , t_{HZ} , t_{OLZ} and t_{OHZ}



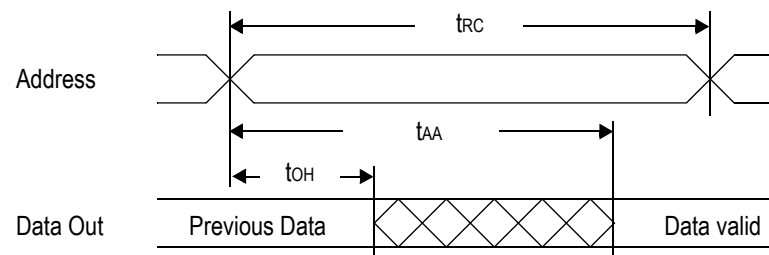
AC Characteristics

Read Cycle

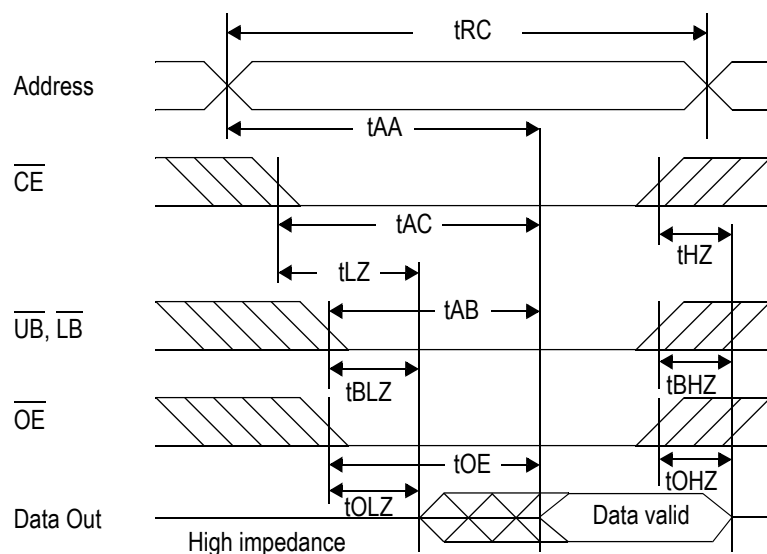
Parameter	Symbol	-6		-8		-10		-12		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Read cycle time	t_{RC}	6	—	8	—	10	—	12	—	ns
Address access time	t_{AA}	—	6	—	8	—	10	—	12	ns
Chip enable access time ($\overline{CE}$)	t_{AC}	—	6	—	8	—	10	—	12	ns
Byte enable access time ($\overline{UB}$, $\overline{LB}$)	t_{AB}	—	3.0	—	3.5	—	4	—	5	ns
Output enable to output valid ($\overline{OE}$)	t_{OE}	—	3.0	—	3.5	—	4	—	5	ns
Output hold from address change	t_{OH}	3	—	3	—	3	—	3	—	ns
Chip enable to output in low Z ($\overline{CE}$)	t_{LZ}^*	3	—	3	—	3	—	3	—	ns
Output enable to output in low Z ($\overline{OE}$)	t_{OLZ}^*	0	—	0	—	0	—	0	—	ns
Byte enable to output in low Z ($\overline{UB}$, $\overline{LB}$)	t_{BLZ}^*	0	—	0	—	0	—	0	—	ns
Chip disable to output in High Z ($\overline{CE}$)	t_{HZ}^*	—	3	—	4	—	5	—	6	ns
Output disable to output in High Z ($\overline{OE}$)	t_{OHZ}^*	—	3.0	—	3.5	—	4	—	5	ns
Byte disable to output in High Z ($\overline{UB}$, $\overline{LB}$)	t_{BHZ}^*	—	3.0	—	3.5	—	4	—	5	—

* These parameters are sampled and are not 100% tested.

Read Cycle 1: $\overline{CE} = \overline{OE} = V_{IL}$, $\overline{WE} = V_{IH}$, $\overline{UB}$ and, or $\overline{LB} = V_{IL}$



Read Cycle 2: $\overline{WE} = V_{IH}$

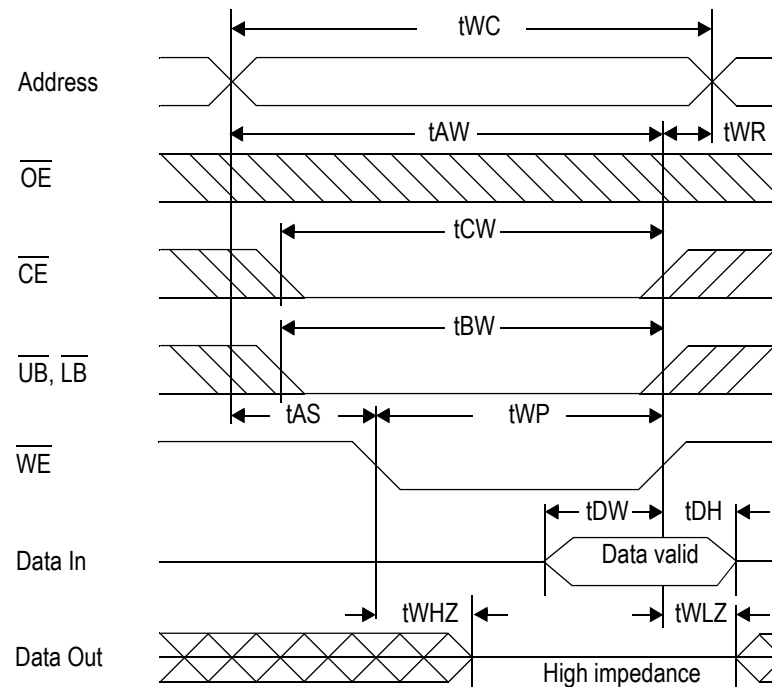


Write Cycle

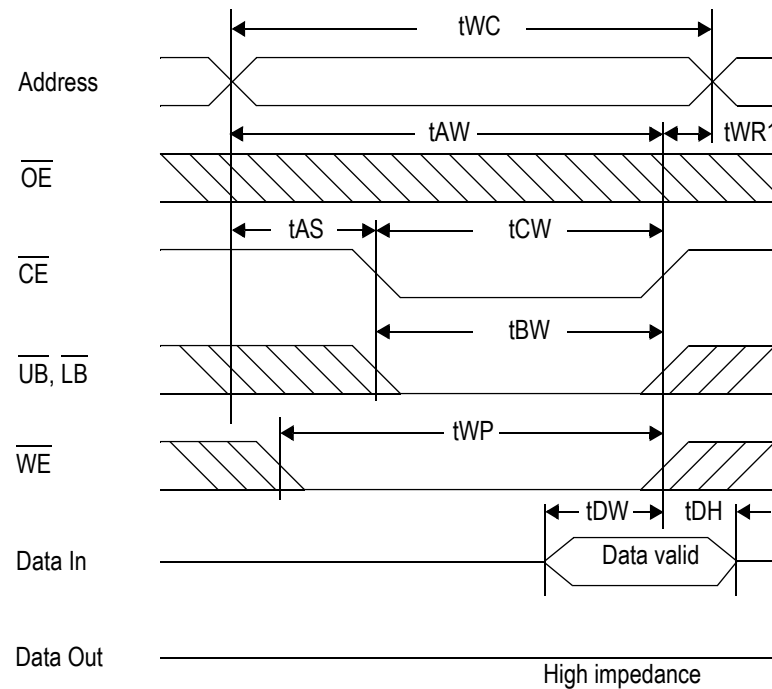
Parameter	Symbol	-6		-8		-10		-12		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Write cycle time	tWC	6	—	8	—	10	—	12	—	ns
Address valid to end of write	tAW	5.0	—	5.5	—	7	—	8	—	ns
Chip enable to end of write	tCW	5.0	—	5.5	—	7	—	8	—	ns
Byte enable to end of write	tBW	5.0	—	5.5	—	7	—	8	—	ns
Data set up time	tDW	3.0	—	4	—	5	—	6	—	ns
Data hold time	tDH	0	—	0	—	0	—	0	—	ns
Write pulse width	tWP	5.0	—	5.5	—	7	—	8	—	ns
Address set up time	tAS	0	—	0	—	0	—	0	—	ns
Write recovery time ($\overline{WE}$)	tWR	0	—	0	—	0	—	0	—	ns
Write recovery time ($\overline{CE}$)	tWR1	0	—	0	—	0	—	0	—	ns
Output Low Z from end of write	tWLZ*	3	—	3	—	3	—	3	—	ns
Write to output in High Z	tWHZ*	—	3.0	—	3.5	—	4	—	5	ns

* These parameters are sampled and are not 100% tested.

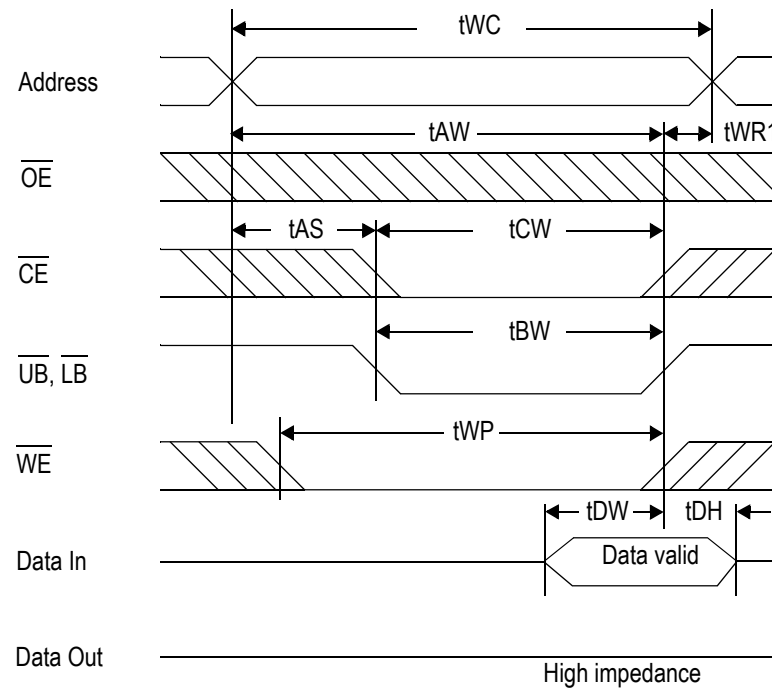
Write Cycle 1: $\overline{\text{WE}}$ control

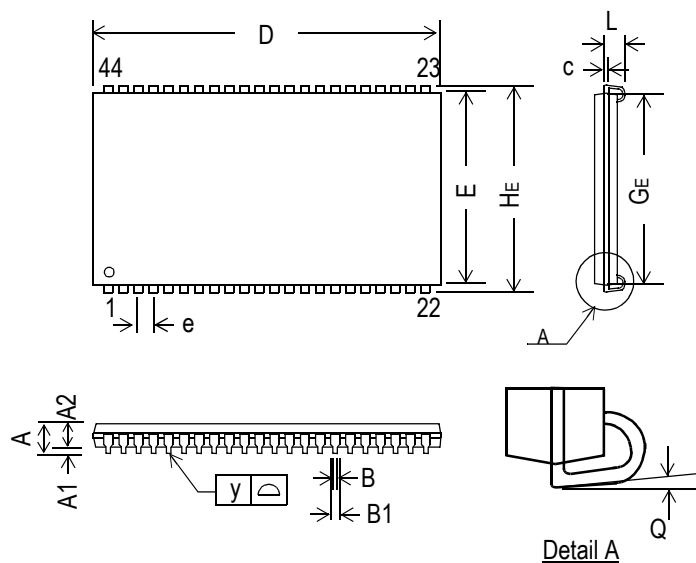


Write Cycle 2: $\overline{\text{CE}}$ control



Write Cycle 3: $\overline{\text{UB}}$, $\overline{\text{LB}}$ control



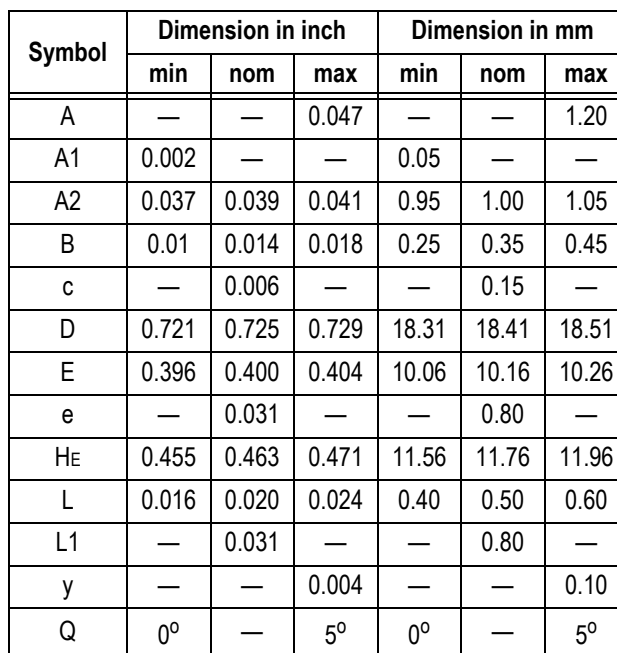
44-Pin, 400 mil SOJ


Symbol	Dimension in inch			Dimension in mm		
	min	nom	max	min	nom	max
A	—	—	0.148	—	—	3.759
A1	0.025	—	—	0.635	—	—
A2	0.105	0.110	0.115	2.667	2.794	2.921
B	—	0.018	—	—	0.457	—
B1	0.026	0.028	0.032	0.660	0.711	0.813
c	—	0.008	—	—	0.203	—
D	1.120	1.125	1.130	28.44	28.58	28.70
E	0.395	0.400	0.405	10.033	10.160	10.287
e	—	0.05	—	—	1.27	—
HE	0.435	0.440	0.445	11.049	11.176	11.303
GE	0.360	0.370	0.380	9.144	9.398	9.652
L	0.082	0.087	0.106	2.083	2.210	2.70
y	—	—	0.004	—	—	0.102
Q	0°	—	7°	0°	—	7°

Notes:

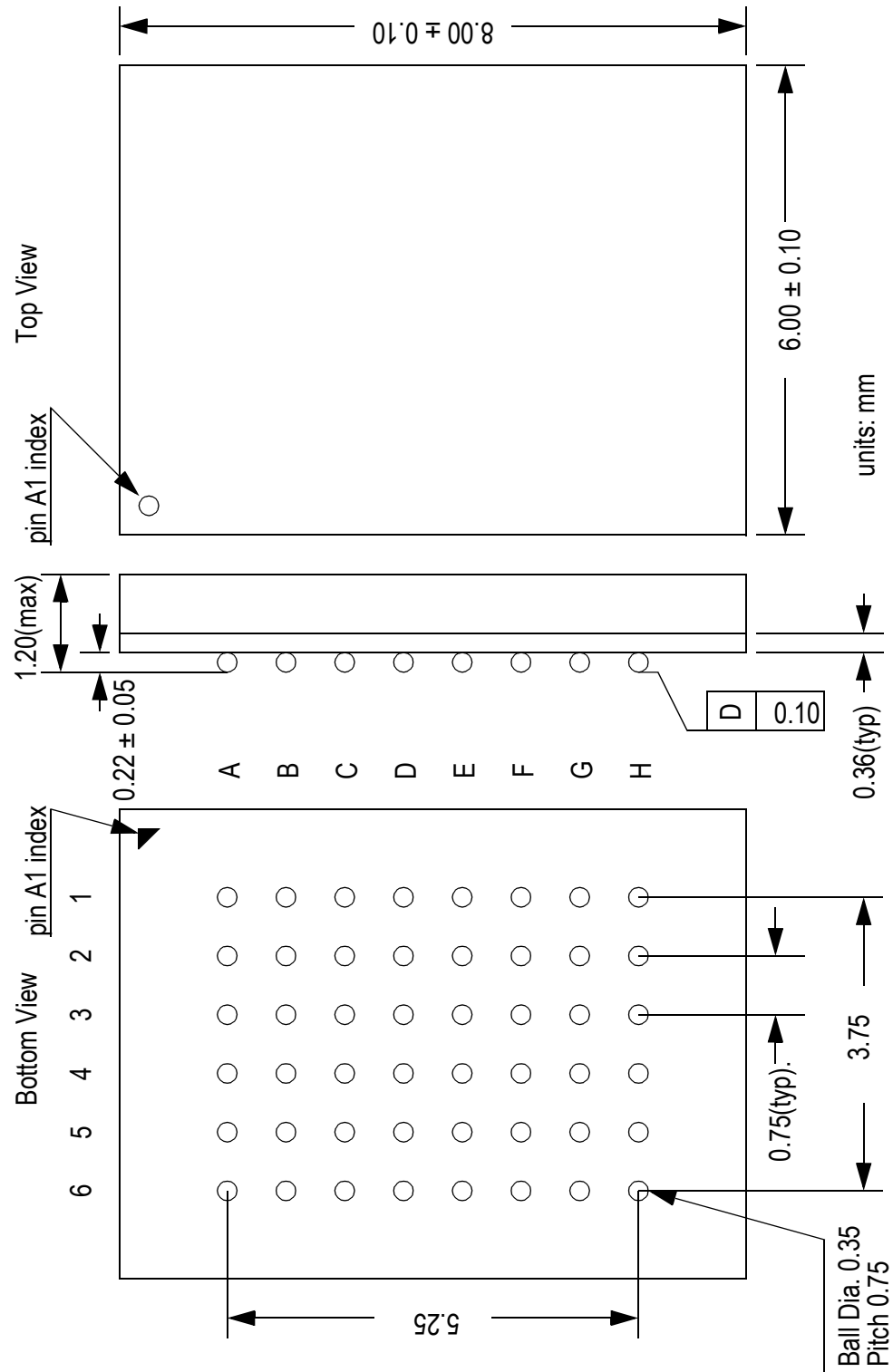
1. Dimension D & E do not include interlead flash.
2. Dimension B1 does not include dambar protrusion/intrusion.
3. Controlling dimension: inches

44 Pin, 400 mil TSOP-II



1. Dimension D & E do not include interlead flash.
2. Dimension B does not include dambar protrusion/intrusion.
3. Controlling dimension: mm

6 mm x 8 mm Fine Pitch BGA



Ordering Information

Part Number *	Package	Access Time	Temp. Range	Status
GS71116ATP-6	400 mil TSOP-II	6 ns	Commercial	
GS71116ATP-8	400 mil TSOP-II	8 ns	Commercial	
GS71116ATP-10	400 mil TSOP-II	10 ns	Commercial	
GS71116ATP-12	400 mil TSOP-II	12 ns	Commercial	
GS71116ATP-6I	400 mil TSOP-II	6 ns	Industrial	
GS71116ATP-8I	400 mil TSOP-II	8 ns	Industrial	
GS71116ATP-10I	400 mil TSOP-II	10 ns	Industrial	
GS71116ATP-12I	400 mil TSOP-II	12 ns	Industrial	
GS71116AJ-6	400 mil SOJ	6 ns	Commercial	
GS71116AJ-8	400 mil SOJ	8 ns	Commercial	
GS71116AJ-10	400 mil SOJ	10 ns	Commercial	
GS71116AJ-12	400 mil SOJ	12 ns	Commercial	
GS71116AJ-6I	400 mil SOJ	6 ns	Industrial	
GS71116AJ-8I	400 mil SOJ	8 ns	Industrial	
GS71116AJ-10I	400 mil SOJ	10 ns	Industrial	
GS71116AJ-12I	400 mil SOJ	12 ns	Industrial	
GS71116AU-6	6 mm x 8 mm Fine Pitch BGA	6 ns	Commercial	
GS71116AU-8	6 mm x 8 mm Fine Pitch BGA	8 ns	Commercial	
GS71116AU-10	6 mm x 8 mm Fine Pitch BGA	10 ns	Commercial	
GS71116AU-12	6 mm x 8 mm Fine Pitch BGA	12 ns	Commercial	
GS71116AU-6I	6 mm x 8 mm Fine Pitch BGA	6 ns	Industrial	
GS71116AU-8I	6 mm x 8 mm Fine Pitch BGA	8 ns	Industrial	
GS71116AU-10I	6 mm x 8 mm Fine Pitch BGA	10 ns	Industrial	
GS71116AU-12I	6 mm x 8 mm Fine Pitch BGA	12 ns	Industrial	

* Customers requiring delivery in Tape and Reel should add the character "T" to the end of the part number. For example:
GS71116ATP-10T

1Mb Asynchronous Datasheet Revision History

Rev. Code: Old; New	Types of Changes Format or Content	Page #/Revisions/Reason
71116A_r1		• Creation of new datasheet
71116A_r1; 71116_r1_01	Content	• Added 6 ns speed bin to entire document
71116A_r1_01; 71116A_r1_02	Content	• Updated all power numbers • Changed 6 mm x 10 mm FPBGA package designator from U to X
71116A_r1_02; 71116A_r1_03	Content	• Updated Recommended Operating Conditions table on page 4 • Changed FPBGA package from 6 x 10 to 6 x 8 (package U) • Updated Read Cycle AC Characteristics table